

General Purpose Transistors

NPN Silicon

We declare that the material of product compliance with RoHS requirements.

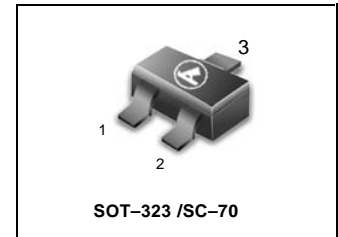
ORDERING INFORMATION (Pb-Free)

Device	Package	Shipping
LBC846AWT1G_S	SC-70	3000/Tape&Reel
LBC846AWT3G_S	SC-70	10000/Tape&Reel

LBC846AWT1G,BWT1G
LBC847AWT1G,BWT1G
CWT1G
LBC848AWT1G,BWT1G
CWT1G

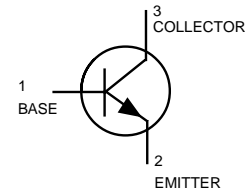
MAXIMUM RATINGS

Rating	Symbol	BC846	BC847	BC848	Unit
Collector-Emitter Voltage	V_{CEO}	65	45	30	V
Collector-Base Voltage	V_{CBO}	80	50	30	V
Emitter-Base Voltage	V_{EBO}	6.0	6.0	5.0	V
Collector Current — Continuous	I_C	100	100	100	mAdc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Total Device Dissipation	P_D	2.4	mW/ $^\circ\text{C}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



DEVICE MARKING

LBC846AWT1G = 1A; LBC846BWT1G = 1B; LBC847AWT1G = 1E; LBC847BWT1G = 1F;
LBC847CWT1G = 1G; LBC848AWT1G = 1J; LBC848BWT1G = 1K; LBC848CWT1G = 1L;

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10\text{ mA}$)	LBC846 Series	65	—	—	v
	LBC847 Series	45	—	—	
	LBC848 Series	30	—	—	
Collector-Emitter Breakdown Voltage ($I_C = 10\ \mu\text{A}, V_{EB} = 0$)	LBC846 Series	80	—	—	v
	LBC847 Series	50	—	—	
	LBC848 Series	30	—	—	
Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}$)	LBC846 Series	80	—	—	v
	LBC847 Series	50	—	—	
	LBC848 Series	30	—	—	
Emitter-Base Breakdown Voltage ($I_E = 1.0\ \mu\text{A}$)	LBC846 Series	6.0	—	—	v
	LBC847 Series	6.0	—	—	
	LBC848 Series	5.0	—	—	
Collector Cutoff Current ($V_{CB} = 30\text{ V}$)	I_{CBO}	—	—	15	nA
		($V_{CB} = 30\text{ V}, T_A = 150^\circ\text{C}$)	—	—	5.0

1.FR-5=1.0 x 0.75 x 0.062in

LBC846AWT1G,BWT1G, LBC847AWT1G,BWT1G, CWT1G, LBC848AWT1G,BWT1G,CWT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10 \mu\text{A}$, $V_{CE} = 5.0 \text{ V}$)	h_{FE}	—	90	—	—
		—	150	—	—
		—	270	—	—
($I_C = 2.0 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$)		110	180	220	
		200	290	450	
		420	520	800	
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}$, $I_B = 5.0 \text{ mA}$)	$V_{CE(sat)}$	—	—	0.25 0.6	V
Base–Emitter Saturation Voltage ($I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}$, $I_B = 5.0 \text{ mA}$)	$V_{BE(sat)}$	—	0.7 0.9	—	V
Base–Emitter Voltage ($I_C = 2.0 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$) ($I_C = 10 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$)	$V_{BE(on)}$	580	660	700 770	mV

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 10 \text{ mA}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	100	—	—	MHz
Output Capacitance ($V_{CB} = 10 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_{obo}	—	—	4.5	pF
Noise Figure ($I_C = 0.2 \text{ mA}$, $V_{CE} = 5.0 \text{ Vdc}$, $R_S = 2.0 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$, $BW = 200 \text{ Hz}$)	NF	—	—	10 4.0	dB

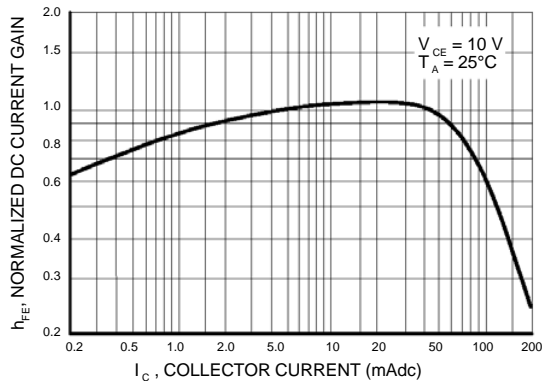


Figure 1. Normalized DC Current Gain

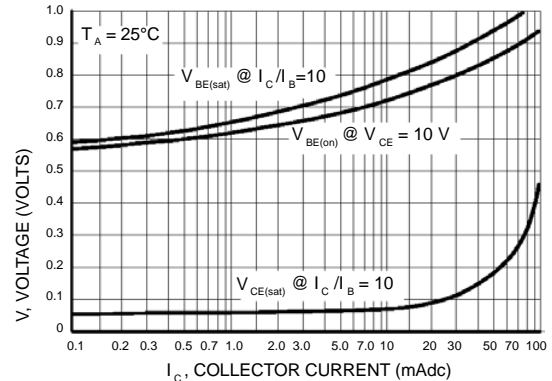


Figure 2. “Saturation” and “On” Voltages

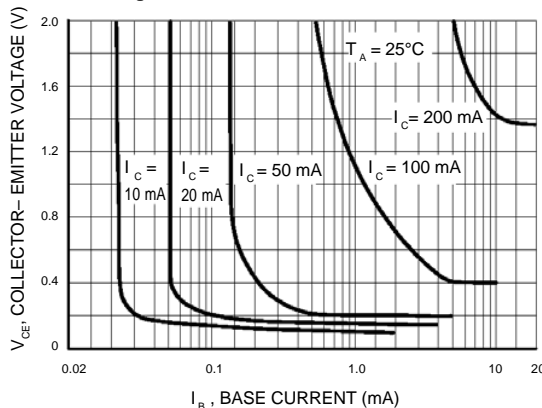


Figure 3. Collector Saturation Region

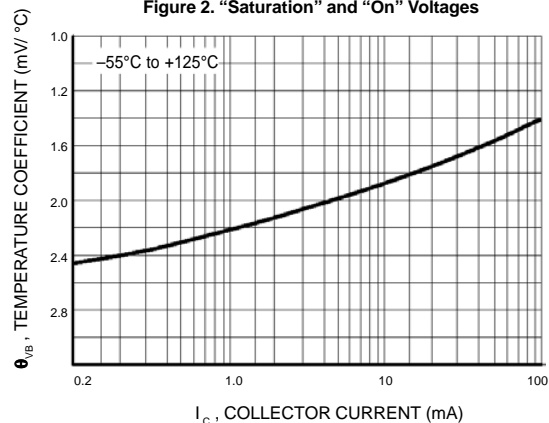


Figure 4. Base–Emitter Temperature Coefficient

LBC846AWT1G,BWT1G, LBC847AWT1G,BWT1G, CWT1G, LBC848AWT1G,BWT1G,CWT1G

LBC847/LBC848

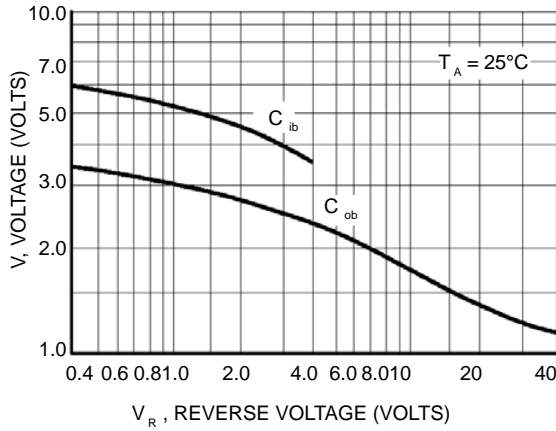


Figure 5. Capacitances

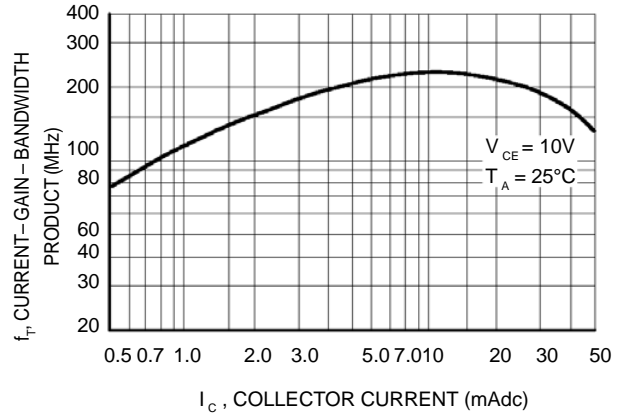


Figure 6. Current-Gain - Bandwidth Product

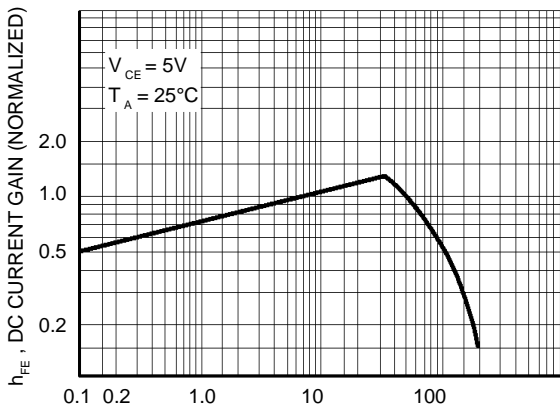


Figure 7. DC Current Gain

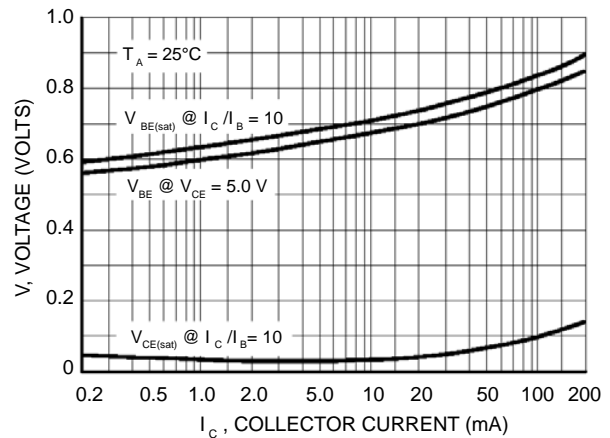


Figure 8. "On" Voltage

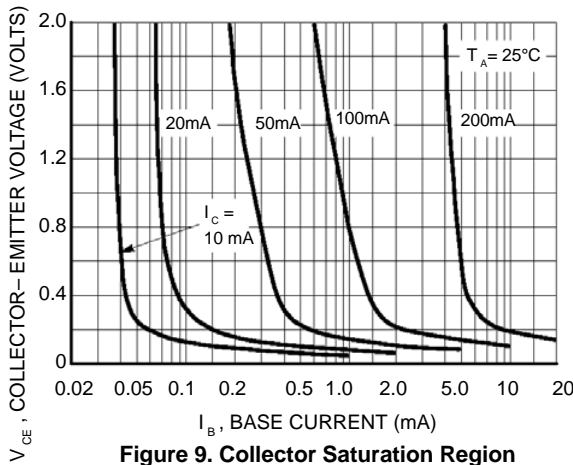


Figure 9. Collector Saturation Region

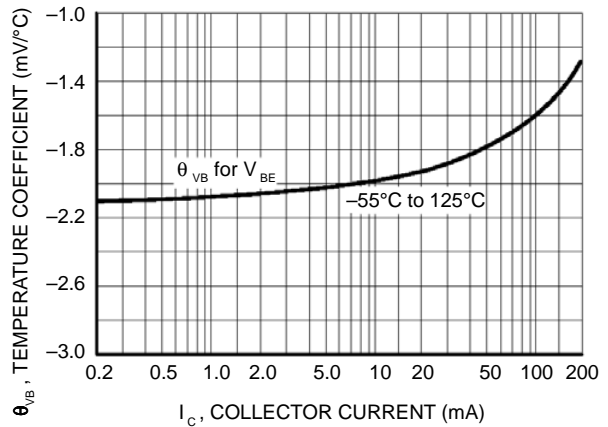


Figure 10. Base-Emitter Temperature Coefficient

LBC846AWT1G,BWT1G, LBC847AWT1G,BWT1G, CWT1G, LBC848AWT1G,BWT1G,CWT1G

LBC846

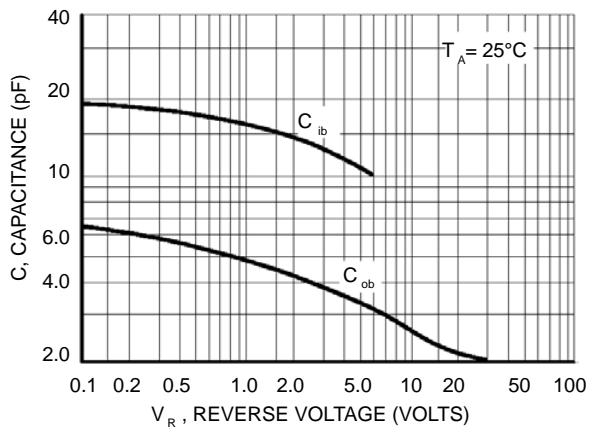


Figure 11. Capacitance

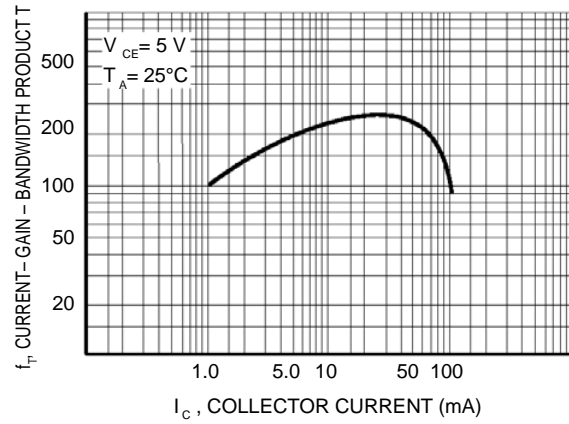


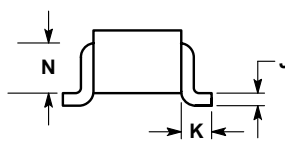
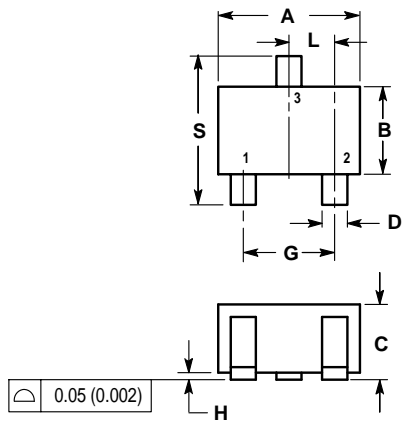
Figure 12. Current-Gain - Bandwidth Product

LBC846AWT1G,BWT1G, LBC847AWT1G,BWT1G, CWT1G, LBC848AWT1G,BWT1G,CWT1G

SC-70 / SOT-323

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

- PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

